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<u>Diodes Incorporated</u> <u>DMMT5551-7-F</u>

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Datasheet of DMMT5551-7-F - TRANS 2NPN 160V 0.2A SOT26

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## **DMMT5551/DMMT5551S**

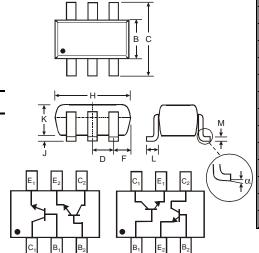
#### MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features**

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance,  $h_{FE},\,V_{CE(SAT)},\,V_{BE(SAT)}$
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

### **Mechanical Data**

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4R & K4T, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



(K4R Marking Code) (K4T Marking Code)

DMMT5551S

SOT-26										
Dim	Min	Max	Тур							
Α	0.35	0.50	0.38							
В	1.50	1.70	1.60							
С	2.70	3.00	2.80							
D			0.95							
F			0.55							
Н	2.90	3.10	3.00							
J	0.013	0.10	0.05							
K	1.00	1.30	1.10							
L	0.35	0.55	0.40							
М	0.10	0.20	0.15							
α	0°	8°	_							
All E	Dimens	ions in	mm							

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current - Continuous (Note 2)	I <sub>C</sub>	200	mA
Power Dissipation (Note 2, 3)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

DMMT5551

#### Notes:

- Built with adjacent die from a single wafer.
- 2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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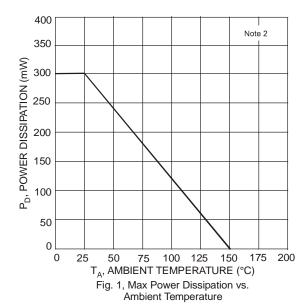


#### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	1				•
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	180		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	160		V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	50	nA μA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0 V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	50	nA	$V_{EB} = 4.0V, I_C = 0$
ON CHARACTERISTICS (Note 7)					
		80	_		$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$
DC Current Gain (Note 8)	h <sub>FE</sub>	80	250	_	$I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V}$
		30	_		$I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.15 0.20	V	$I_C = 10mA$ , $I_B = 1.0mA$
Concolor Emilier Calaration Voltage	V CE(SAT)				$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V25(0.47)		1.0	V	$I_C = 10mA$ , $I_B = 1.0mA$
•	V <sub>BE(SAT)</sub>	_	1.0	V	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_obo$	_	6.0	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$
Small Signal Current Gain	h <sub>FE</sub>	50	250	_	$V_{CE} = 10V, I_{C} = 1.0mA,$ f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	$V_{CE} = 10V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE} = 5.0V$ , $I_{C} = 200\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$

Notes:

- Short duration pulse test used to minimize self-heating effect. The DC Current Gain,  $h_{FE}$ , (matched at  $I_C = 10$ mA and  $V_{CE} = 5$ V) Collector Emitter Saturation Voltage,  $V_{CE(SAT)}$ , and Base Emitter Saturation Voltage,  $V_{BE(SAT)}$  are matched with typical matched tolerances of 1% and maximum of 2%.



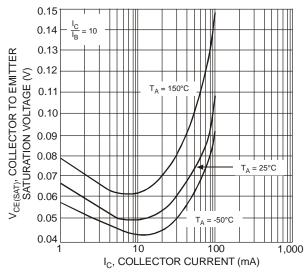


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

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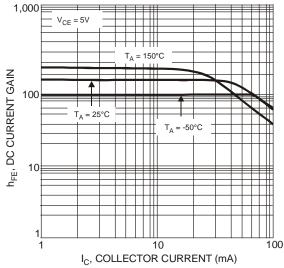


Fig. 3, DC Current Gain vs. Collector Current

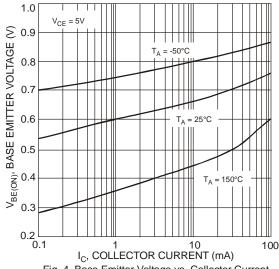


Fig. 4, Base Emitter Voltage vs. Collector Current

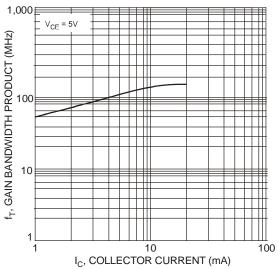


Fig. 5, Gain Bandwidth Product vs. Collector Current

### Ordering Information (Note 6 & 9)

Device	Packaging	Shipping
DMMT5551-7-F	SOT-26	3000/Tape & Reel
DMMT5551S-7-F	SOT-26	3000/Tape & Reel

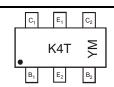
Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**



K4R = DMMT5551 Product Type Marking Code YM = Date Code Marking

Y = Year ex: T = 2006 M = Month ex: 9 = September



K4T = DMMT5551S Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006

M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	T	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



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